

P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
- 30	0.053 at V _{GS} = - 10 V	- 4.0
	0.086 at V _{GS} = - 4.5 V	- 3.1

FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET

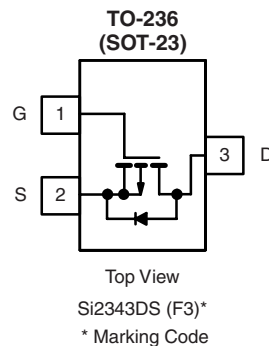


Available
RoHS*
COMPLIANT

HALOGEN
FREE
Available

APPLICATIONS

- Load Switch
- PA Switch



Ordering Information: Si2343DS-T1
Si2343DS-T1-E3 (Lead (Pb)-free)
Si2343DS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	5 s	Steady State	Unit
Drain-Source Voltage	V _{DS}	- 30		V
Gate-Source Voltage	V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C) ^{a, b}	I _D	T _A = 25 °C	- 4.0	- 3.1
		T _A = 70 °C	- 3.2	- 2.5
Pulsed Drain Current	I _{DM}	- 15		A
Continuous Source Current (Diode Conduction) ^{a, b}	I _S	- 1.0	- 0.6	
Maximum Power Dissipation ^{a, b}	P _D	T _A = 25 °C	1.25	0.75
		T _A = 70 °C	0.8	0.48
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R _{thJA}	t ≤ 5 s	75	100	°C/W
		Steady State	120	166	
Maximum Junction-to-Foot (Drain)	R _{thJF}	40	50		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. Pulse width limited by maximum junction temperature.

* Pb containing terminations are not RoHS compliant, exemptions may apply

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 30			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 1		- 3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}$			- 1	μA
		$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			- 10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -10\text{ V}$	- 15			A
Drain-Source On-Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -4.0\text{ A}$		0.043	0.053	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -3.1\text{ A}$		0.068	0.086	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -5\text{ V}, I_D = -4.0\text{ A}$		10		S
Diode Forward Voltage	V_{SD}	$I_S = -1.0\text{ A}, V_{GS} = 0\text{ V}$		- 0.7	- 1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}$ $I_D \cong -4.0\text{ A}$		14	21	nC
Gate-Source Charge	Q_{gs}			1.9		
Gate-Drain Charge	Q_{gd}			3.7		
Input Capacitance	C_{iss}	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		540		pF
Output Capacitance	C_{oss}			131		
Reverse Transfer Capacitance	C_{rss}			105		
Switching^c						
Turn-On Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong -1.0\text{ A}, V_{GEN} = -10\text{ V}$ $R_G = 6\text{ }\Omega$		10	15	ns
	t_r			15	25	
Turn-Off Time	$t_{d(off)}$			31	50	
	t_f			20	30	

Notes:

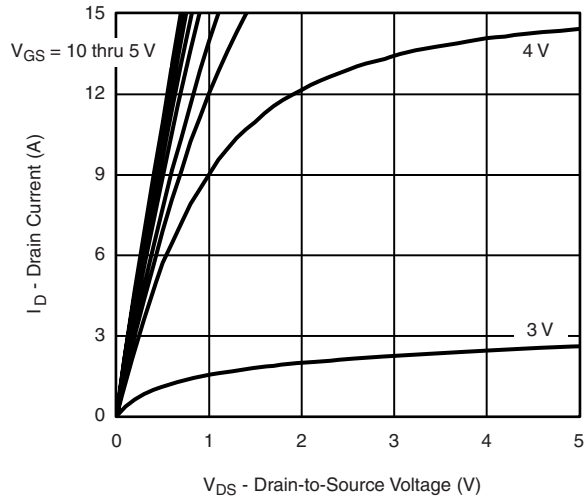
a. Pulse test: $PW \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. For DESIGN AID ONLY, not subject to production testing.

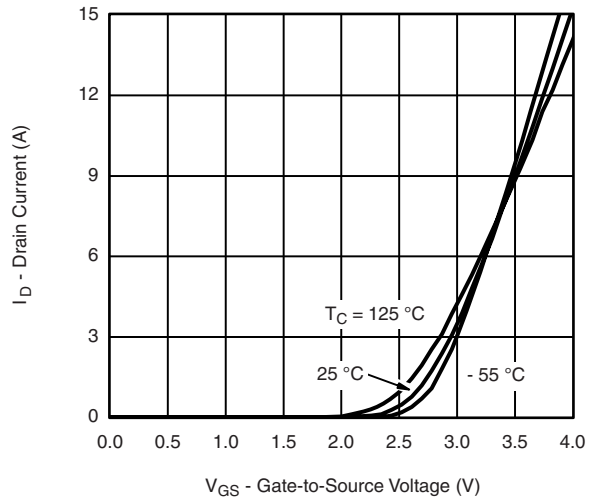
c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

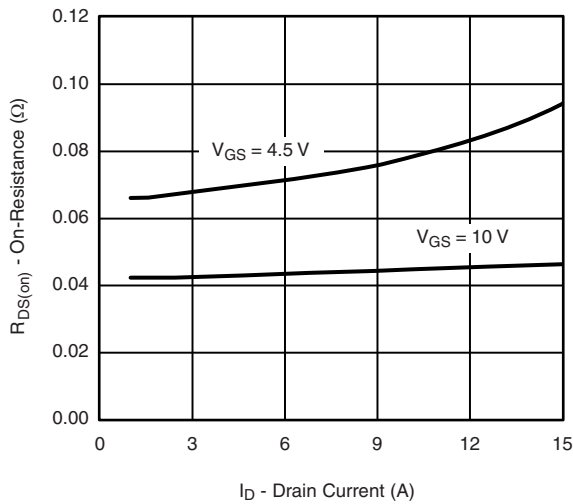
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



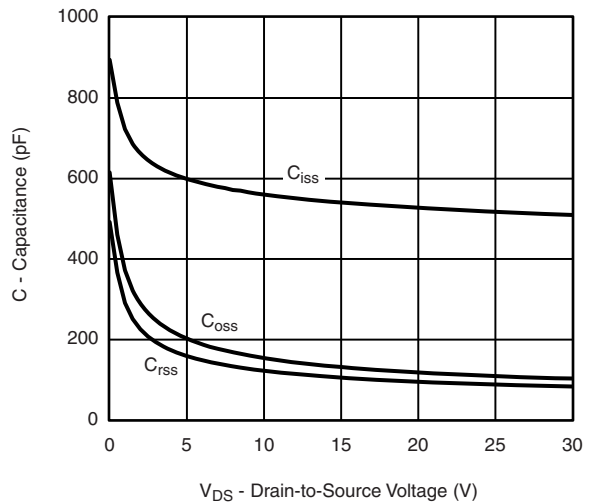
Output Characteristics



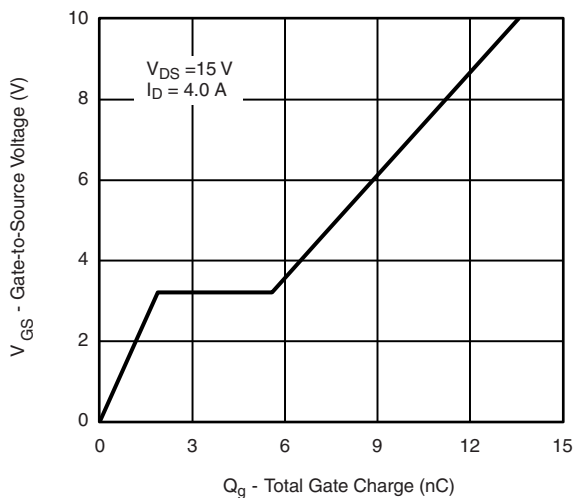
Transfer Characteristics



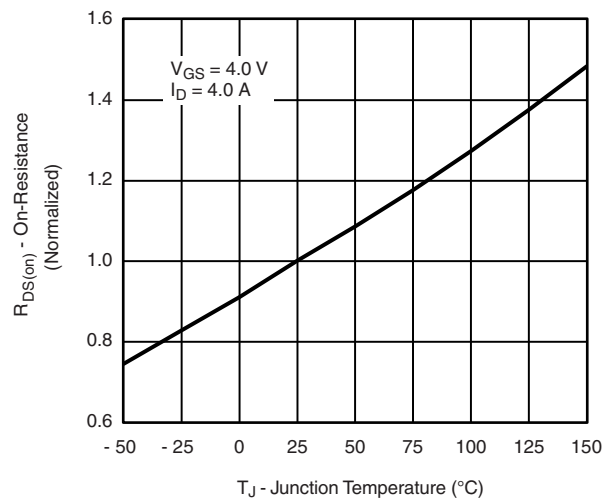
On-Resistance vs. Drain Current



Capacitance

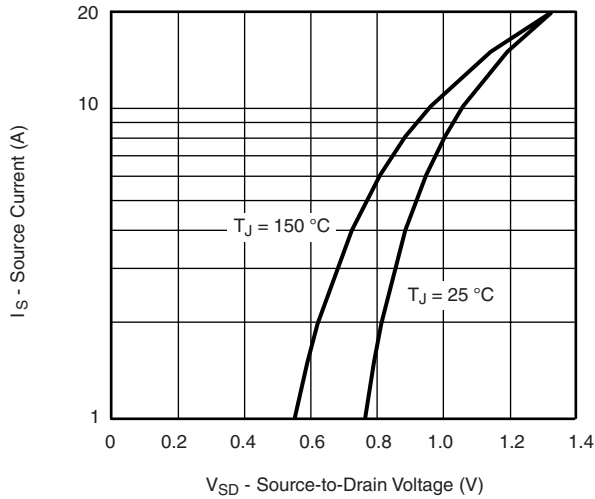


Gate Charge

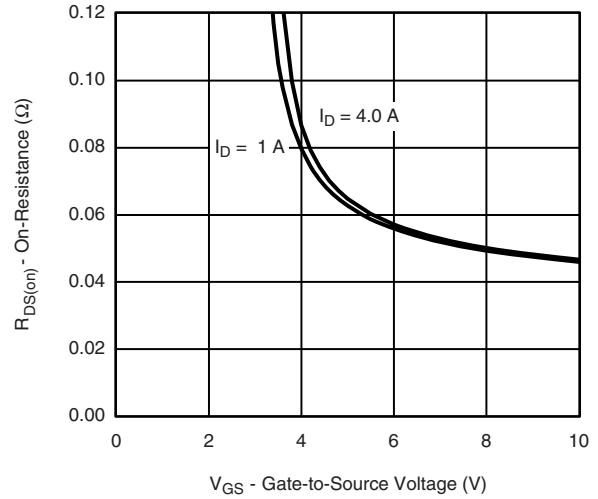


On-Resistance vs. Junction Temperature

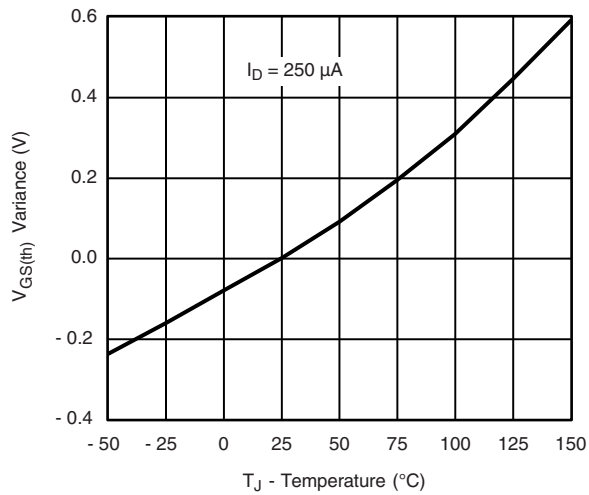
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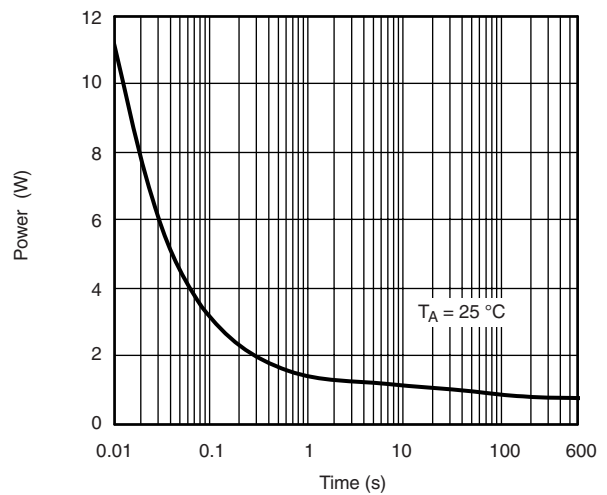
Source-Drain Diode Forward Voltage



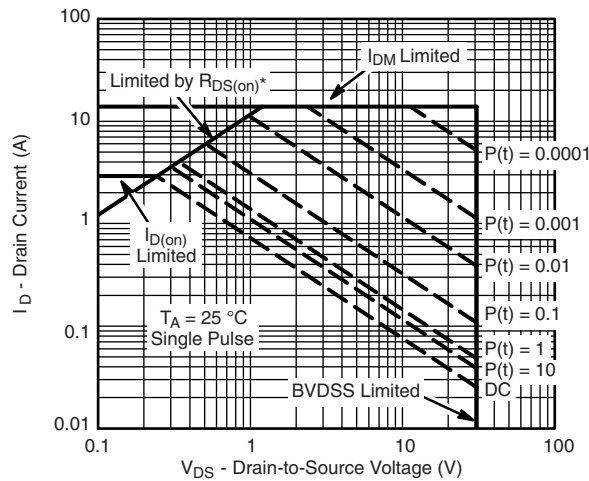
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



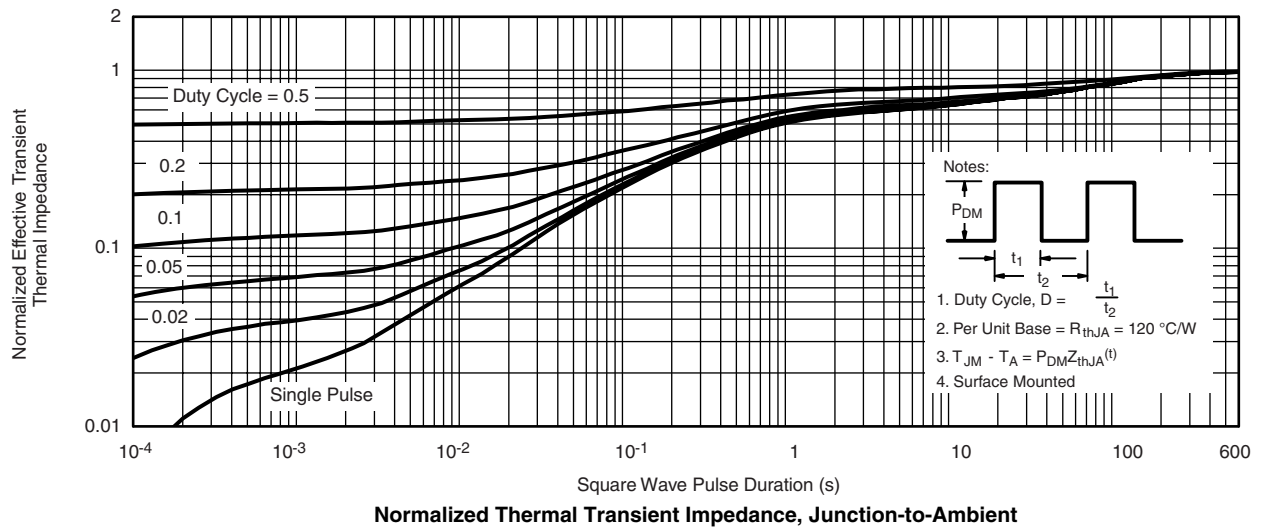
Single Pulse Power



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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